

### INCHANGE SEMICONDUCTOR

### **isc** Silicon NPN Power Transistors

## D44H8

#### DESCRIPTION

- Low Saturation Voltage
- Fast Switching Speeds
- Minimum Lot-to-Lot variations for robust device performance and reliable operation

### **APPLICATIONS**

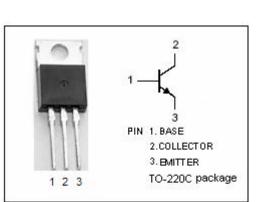
• Designed for general purpose power amplification and switching such as output or driver stages in applications such as switching regulators, converters and power amplifier.

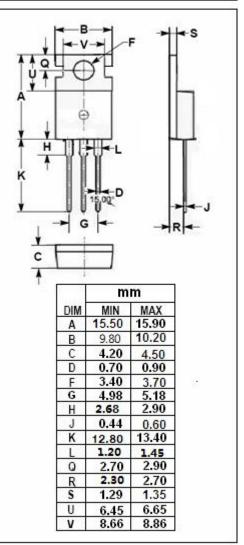
#### ABSOLUTE MAXIMUM RATINGS(Ta=25℃)

SYMBOL	PARAMETER	VALUE	UNIT		
VCEO	Collector-Emitter Voltage	60	V		
V <sub>EBO</sub>	Emitter-Base Voltage	5	V		
Ic	Collector Current-Continuous	10	А		
Ісм	Collector Current-Peak	20	А		
Pc	Collector Power Dissipation @Tc=25°C	50	W		
Tj	Junction Temperature	150	°C		
T <sub>stg</sub>	Storage Temperature Range	-55~150	°C		

#### THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	МАХ	UNIT	
Rth j-c	Thermal Resistance, Junction to Case	2.5	°C/W	
R <sub>th j-a</sub>	Thermal Resistance, Junction to Ambient	75	°C/W	







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### **ELECTRICAL CHARACTERISTICS**

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SYMBOL	PARAMETER	CONDITIONS	MIN	ТҮР	МАХ	UNIT
V <sub>CE(sat)</sub>	Collector-EmitterSaturation Voltage	I <sub>C</sub> = 8A ;I <sub>B</sub> = 0.8 A			1	v
V <sub>BE(sat)</sub>	Base-Emitter Saturation Voltage	I <sub>C</sub> = 8A ;I <sub>B</sub> = 0.8 A			1.5	V
I <sub>CES</sub>	Collector Cutoff Current	V <sub>CE</sub> =Rated V <sub>CEO</sub> ;			10	μA
I <sub>EBO</sub>	Emitter Cutoff Current	V <sub>EB</sub> = 5V; I <sub>C</sub> = 0			100	μA
h <sub>FE-1</sub>	DC Current Gain	I <sub>C</sub> = 2A ; V <sub>CE</sub> = 1V	60			
h <sub>FE-2</sub>	DC Current Gain	I <sub>C</sub> = 4A ; V <sub>CE</sub> = 1V	40			
Сов	Output Capacitance	V <sub>CB</sub> = 10V,f= 0.1MHz		130		pF
f⊤	Current-Gain—Bandwidth Product	I <sub>C</sub> = 0.5A;V <sub>CE</sub> = 10V;f <sub>test</sub> =20MHz		50		MHz

#### Switching Times

ts	Storage Time	I <sub>C</sub> = 5A; I <sub>B1</sub> = -I <sub>B2</sub> = 0.5A V <sub>CC</sub> = 20V	0.5	μ <b>s</b>
t <sub>f</sub>	Fall Time		0.14	μ <b>S</b>

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